

Vishay Siliconix

Powered-off Protection, 1 Ω , 1.8 V to 5.5 V, SPDT Analog Switch (2:1 Multiplexer)

DESCRIPTION

The DG2012E is a high performance single-pole, double-throw (SPDT) analog switch designed for 1.8 V to 5.5 V operation with a single power rail.

Fabricated with high density CMOS technology, the device achieves low on resistance of 1 Ω at a 5 V power supply, low power consumption, and fast switching speeds.

The DG2012E can handle both analog and digital signals and permits signals with amplitudes of up to V+ to be transmitted in either direction. Its control logic inputs can go over V+ up to 5.5 V. It features break before make switching performance. Its -3 dB bandwidth is typically 160 MHz.

A powered-off protection circuit is built into the switch to prevent an abnormal current flow from COM pin to V+ during the power-down condition. Each output pin can withstand greater than 7 kV (human body model).

Operation temperature is specified from -40 °C to +85 °C. The DG2012E is available in SC-70-6L package.

FEATURES

- Low switch on-resistance (1 Ω)
- 1.65 V to 5.5 V single supply operation
- Isolation in powered-off mode
- Control logic inputs can go over V+
- Low charge injection (5 pC)
- · Low total harmonic distortion
- Break before make switching
- Latch-up performance exceeds 300 mA per JESD 78
- ESD tested
 - 7000 V human body model (JS-001)
 - 1000 V charge device model (JS-002)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

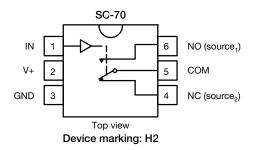
Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

APPLICATIONS

- Smartphones and tablets
- Consumer and computing
- Portable instrumentation
- · Medical equipment

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Pin 1 —	H2XXX	
Device markin XXX = date / lo	g: H2XXX ot traceability co	ode

TRUTH TABLE				
LOGIC	NC	NO		
0	On	Off		
1	Off	On		

ORDERING INFORMATION				
TEMP. RANGE	PACKAGE	PART NUMBER		
-40 °C to +85 °C	SC-70-6	DG2012EDL-T1-GE3		

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ABSOLUTE MAXIMUM RATINGS					
PARAMETER		LIMIT	UNIT		
V+, COM, NC, NO, IN reference to GND		-0.3 to 6	V		
Continuous current (NO, NC, and COM pins)		± 100	mA		
Peak current (pulsed at 1 ms, 10 % duty cycle	± 300	IIIA			
Storage temperature (D suffix)		-65 to +150	°C		
Power dissipation (packages) ^a	6-pin SO-70 ^b	250	mW		
ESD / HBM JS-001		7000	V		
ESD / CDM	JS-002	1000	\ \ \		
Latch up	Per JESD78 with 1.5 x voltage clamp	300	mA		

Notes

- a. All leads welded or soldered to PC board b. Derate 3.1 mW/°C above 70 °C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS (V+	= 5 V)						
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. a		°C to +8		UNIT
Annalan Conitale		$V+ = 5 V$, $\pm 10 \%$, $V_{IN} = 0.8 V$ or 2.4 V^e		MIN. b	TYP. c	MAX. b	
Analog Switch				I	I	I	
Analog signal range d	$V_{NO}, V_{NC} \ V_{COM}$		Full	0	-	V+	V
On-resistance	R _{ON}	$V_{+} = 4.5 \text{ V},$ $V_{COM} = 0.5 \text{ V} / 2.5 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room Full ^d	-	1	1.6	
R _{ON} flatness ^d	R _{ON} flatness	V+ = 4.5 V,	Room	-	0.2	0.5	Ω
R _{ON} match ^d	ΔR_{ON}	$V_{COM} = 0 \text{ V to V+}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room	-	=	0.3	
	I _{NO(off)}		Room	-5	-	5	
0 11 11 11	I _{NC(off)}	V+ = 5 V	Full	-20	=	20	
Switch off leakage current f		V_{NO} , $V_{NC} = 0.5 \text{ V} / 4.5 \text{ V}$, $V_{COM} = 4.5 \text{ V} / 0.5 \text{ V}$	Room	-5	-	5	
	ICOM(off)	VCOM = 4.5 V / 5.5 V	Full ^d	-20	=	20	nA
		V+ = 5 V,	Room	-5	=	5	-
Channel-on leakage current f	I _{COM(on)}	V_{NO} , $V_{NC} = V_{COM} = 0.5 \text{ V} / 4.5 \text{ V}$	Full d	-20	-	20	
Power down leakage	I _{COM(PD)}	$V+ = 0 V, V_{COM} = 4.5 V, V_{IN} = GND$	Full d	-1	-	1	μΑ
Digital Control	, , ,			I.	I.	I.	
Input high voltage	V_{INH}		Full	2.4	-	-	V
Input low voltage	V _{INL}		Full	-	-	0.8	V
Input capacitance d	C _{IN}		Full	-	3	-	pF
Input current f	I _{INL} or I _{INH}	$V_{IN} = 0 \text{ V or V} +$	Full	-1	-	1	μA
Dynamic Characteristics							
Turn-on time d	1		Room	=	15	32	
Turn-on time ⁹	t _{ON}	V_{NO} or $V_{NC} = 3 V$,	Full ^d	-	-	35	
Turn-off time d		$R_L = 300 \Omega$, $C_L = 35 pF$	Room	-	7	28	ns
rum-on time «	t _{OFF}		Full ^d	-	-	30	
Break-before-make time d	t _d		Room	1	5	-	
Charge injection ^d	Q _{INJ}	$C_L = 1 \text{ nF}, V_{GEN} = 0 \text{ V}, R_{GEN} = 0 \Omega$	Room	-	8	-	рС
Off-isolation d	OIRR	D 5000 5-54 4MH	Room	-	-63	-	٩D
Crosstalk d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room	-	-63	-	dB
N _O , N _C off capacitance ^d	$C_{NO(off)} \ C_{NC(off)}$	$V_{IN} = 0 \text{ V or V+, f} = 1 \text{ MHz}$	Room	-	16	-	pF
Channel-on capacitance d	C _{ON}		Room	-	52	-	
Power Supply	<u> </u>		•				
Power supply current	l+	V _{IN} = 0 V or V+	Full	-	0.0003	1	μA



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PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. a	LIMITS -40 °C to 85 °C			UNIT
		V+ = 3 V, \pm 10 %, V _{IN} = 0.4 V or 1.4 V $^{\rm e}$		MIN. b	TYP. °	MAX. b	
Analog Switch			•				
Analog signal range ^d	$V_{NO}, V_{NC} \ V_{COM}$		Full	0	-	V+	V
On-resistance	R _{ON}	$V_{+} = 2.7 \text{ V},$ $V_{COM} = 0.2 \text{ V} / 1.5 \text{ V}, I_{NO} I_{NC} = 10 \text{ mA}$	Room Full ^d	-	1.4	2.5	
R _{ON} flatness ^d	R _{ON} flatness	V+ = 2.7 V,	Room	-	0.6	0.9	Ω
R _{ON} match ^d	ΔR_{ON}	$V_{COM} = 0 V \text{ to V+}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room	-	-	0.3	
	I _{NO(off)}		Room	-5	-	5	
O State of Land and a constit	I _{NC(off)}	V+ = 3.3 V	Full	-15	-	15	
Switch off leakage current f		V_{NO} , V_{NC} = 1 V / 3 V, V_{COM} = 3 V / 1 V	Room	-5	-	5	
	ICOM(off)		Full ^d	-15	-	15	nA
0, , , , , , , , , , , , , , , , , , ,		V+ = 3.3 V.	Room	-5	-	5	
Channel-on leakage current f	I _{COM(on)}	V_{NO} , $V_{NC} = V_{COM} = 1 \text{ V} / 3 \text{ V}$	Full ^d	-15	-	15	
Digital Control				l	l .		L
Input high voltage	V _{INH}		Full	1.4	-	-	V
Input low voltage	V_{INL}		Full	-	-	0.4	V
Input capacitance d	C _{IN}		Full	-	3	-	pF
Input current f	I _{INL} or I _{INH}	V _{IN} = 0 V or V+	Full	-1	-	1	μΑ
Dynamic Characteristics	·						
Turn-on time d	+		Room	-	21	42	
rum-on time -	t _{ON}	V V 0V	Full ^d	-	-	47	
Turn-off time d	+	V_{NO} or $V_{NC} = 2 V$, $R_L = 300 \Omega$, $C_L = 35 pF$	Room	-	16	32	ns
Turr-on time -	t _{OFF}		Full ^d	-	-	35	
Break-before-make time ^d	t _d		Room	1	7	-	
Charge injection ^d	Q _{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω	Room	-	6	-	рС
Off-isolation ^d	OIRR		Room	-	-63	-	dB
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega, C_L = 5 pF, f = 1 MHz$	Room	-	-63	-	ub
Bandwidth ^d	BW		Room	-	160	-	MHz
N _O , N _C off capacitance ^d	C _{NO(off)} C _{NC(off)}	V _{IN} = 0 V or V+, f = 1 MHz	Room	-	16	-	pF
Channel-on capacitance d	C _{ON}	,	Room	-	52	-	•
Power Supply							
Power supply current	l+	$V_{IN} = 0 \text{ V or V} +$	Full	_	0.00002	1	μA



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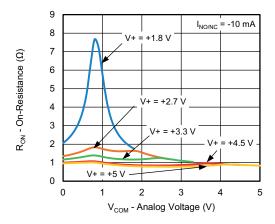
SPECIFICATIONS (V+	= 2 V)						
PARAMETER	SYMBOL	TEST CONDITIONS UNLESS OTHERWISE SPECIFIED	TEMP. a	LIMITS -40 °C to +85 °C			UNIT
		$V+ = 2 V$, $\pm 10 \%$, $V_{IN} = 0.4 V$ or 1.6 V^e		MIN. b	TYP. c	MAX. b	
Analog Switch							
Analog signal range ^d	$V_{ m NO}, V_{ m NC}, \ V_{ m COM}$		Full	0	-	V+	٧
On-resistance	R _{ON}	$V+ = 1.8 \text{ V}, V_{COM} = 0.2 \text{ V} / 0.9 \text{ V}$ $I_{NO}, I_{NC} = 10 \text{ mA}$	Room Full ^d	-	5	10 15	
R _{ON} flatness ^d	R _{ON} flatness	V+ = 1.8 V, V _{COM} = 0 V to V+,	Room	-	6	9	Ω
R _{ON} match ^d	ΔR_{ON}	I_{NO} , $I_{NC} = 10 \text{ mA}$	Room	-	-	0.3	
	I _{NO(off)}		Room	-0.5		0.5	
O State of Local account of	I _{NC(off)}	V + = 2.2 V	Full	-5	-	5	
Switch off leakage current f		V_{NO} , $V_{NC} = 0.5 \text{ V} / 1.5 \text{ V}$, $V_{COM} = 1.5 \text{ V} / 0.5 \text{ V}$	Room	-0.5	-	0.5	- 4
	I _{COM(off)}	- COM THE TY STEET	Full ^d	-5	-	5	nA
Channel on leakage augment f		V+ = 2.2 V, $V_{NO}, V_{NC} = V_{COM} = 0.5 \text{ V} / 1.5 \text{ V}$	Room	-0.5	-	0.5	
Channel-on leakage current †	I _{COM(on)}		Full ^d	-5	-	5	
Digital Control							
Input high voltage	V_{INH}		Full	1.6	-	-	V
Input low voltage	V_{INL}		Full	-	-	0.4	٧
Input capacitance d	C_{IN}		Full	-	3	-	pF
Input current f	I_{INL} or I_{INH}	$V_{IN} = 0 \text{ V or V} +$	Full	-1	-	1	μΑ
Dynamic Characteristics							
Turn-on time d	t _{ON}		Room	-	37	57	
rum on time	UN	VV 45V	Full ^d	-	-	60	
Turn-off time d	t _{OFF}	V_{NO} or $V_{NC} = 1.5 \text{ V}$, $R_1 = 300 \Omega$, $C_1 = 35 \text{ pF}$	Room	-	26	44	ns
Turri on time	OFF	, ,,	Full ^d	-	-	45	
Break-before-make time ^d	t _d		Room	1	17	-	
Charge injection d	Q_{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω	Room	-	21	-	рС
Off-isolation d	OIRR	$R_1 = 50 \Omega, C_1 = 5 pF, f = 1 MHz$	Room	-	-63	-	dB
Crosstalk ^d	X_{TALK}	35, 5 <u>L</u> - 5 pr, 1 = 1 1111 12	Room	-	-63	-	
N _O , N _C off capacitance ^d	${\sf C}_{\sf NO(off)} \ {\sf C}_{\sf NC(off)}$	$V_{IN} = 0 V \text{ or } V+, f = 1 MHz$	Room	-	16	-	pF
Channel-on capacitance d	C _{ON}		Room	-	51	-	
Power Supply							
Power supply current	l+	$V_{IN} = 0 V \text{ or } V+$	Full	-	0.00001	1	μΑ

Notes

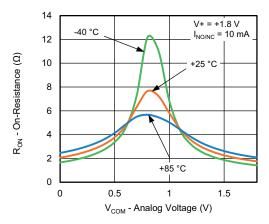
- a. Room = 25 °C, full = as determined by the operating suffix
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet
- c. Typical values are for design aid only, not guaranteed nor subject to production testing
- d. Guarantee by design, nor subjected to production test
- e. V_{IN} = input voltage to perform proper function
- f. Guaranteed by 5 V leakage testing, not production tested



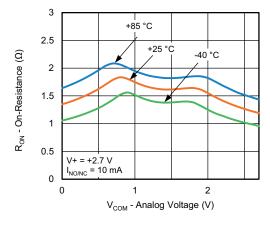
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



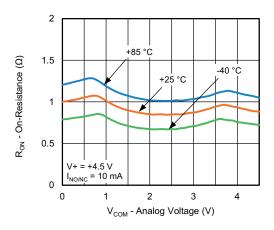
R_{ON} vs. V_{COM} and Supply Voltage



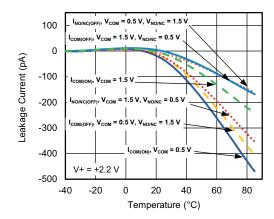
 R_{ON} vs. V_{COM} and Temperature



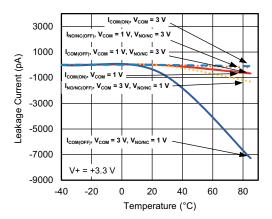
 R_{ON} vs. V_{COM} and Temperature



 R_{ON} vs. V_{COM} and Temperature



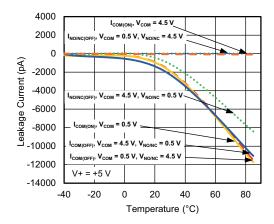
Leakage Current vs. Temperature



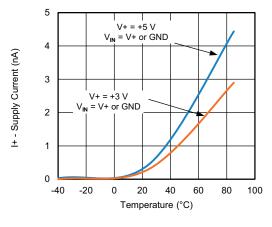
Leakage Current vs. Temperature



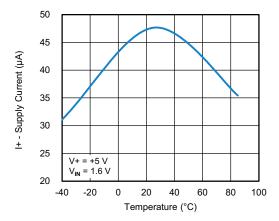
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



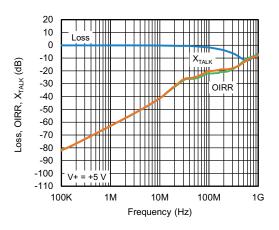
Leakage Current vs. Temperature



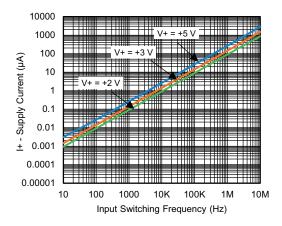
Supply Current vs. Temperature



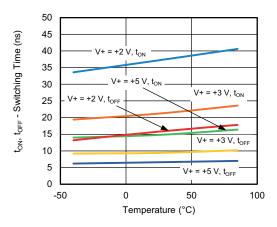
Supply Current vs. Temperature



Insertion Loss, Off-Isolation Crosstalk vs. Frequency



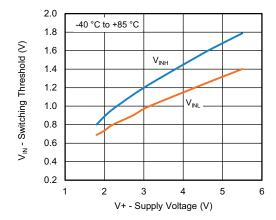
Supply Current vs. Input Switching Frequency



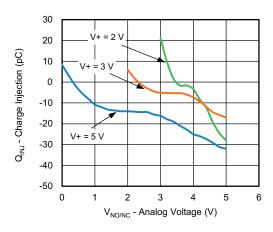
Switching Time vs. Temperature and Supply Voltage



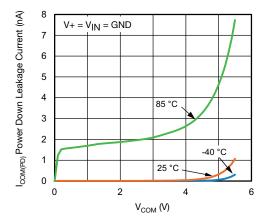
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



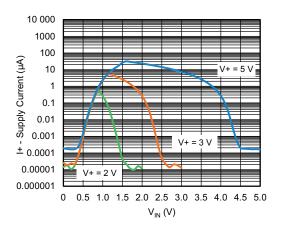
Switching Threshold vs. Supply Voltage



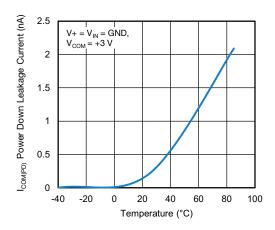
Charge Injection vs. Analog Voltage



Power Down Leakage Current vs. V_{COM}



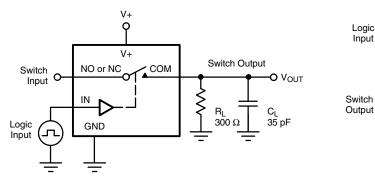
Supply Current vs. Enable Input Voltage



Power Down Leakage Current vs. Temperature

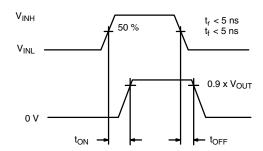


TEST CIRCUITS



C_L (includes fixture and stray capacitance)

$$V_{OUT} = V_{COM} \left(\frac{R_L}{R_L + R_{ON}} \right)$$



Logic "1" = Switch On

Logic input waveforms inverted for switches that have the opposite logic sense.



Input

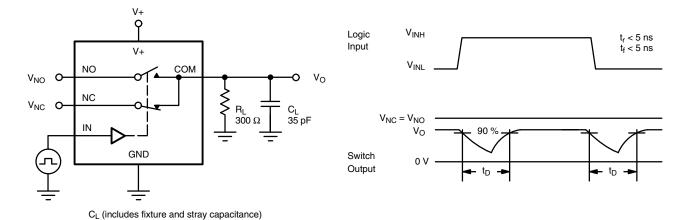
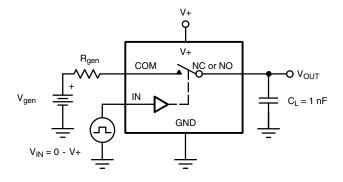
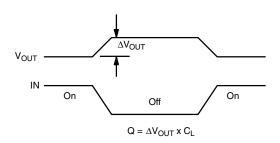


Fig. 2 - Break-Before-Make Interval





IN depends on switch configuration: input polarity determined by sense of switch.

Fig. 3 - Charge Injection

Off Isolation = 20 log $\frac{CC...}{V_{NO/NC}}$

Analyzer

TEST CIRCUITS

V+ V+ NC or NO COM O V, 2.4 V

Fig. 4 - Off-Isolation

GND

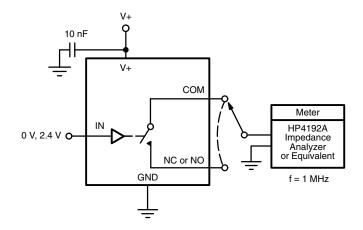


Fig. 5 - Channel Off / On Capacitance



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PRODUCT SUMMARY		
Part number	DG2012E	
Status code	2	
Configuration	SPDT x 2	
Single supply min. (V)	1.65	
Single supply max. (V)	5.5	
Dual supply min. (V)	-	
Dual supply max. (V)	-	
On-resistance (Ω)	1	
Charge injection (pC)	8	
Source on capacitance (pF)	52	
Source off capacitance (pF)	16	
Leakage switch on typ. (nA)	1.4	
Leakage switch off max. (nA)	5	
-3 dB bandwidth (MHz)	160	
Package	SC-70-6	
Functional circuit / applications	Multi purpose, instrumentation, medical and healthcare, portable	
Interface	Parallel	
Single supply operation	Yes	
Dual supply operation	-	
Turn on time max. (ns)	47	
Crosstalk and off isolation	-41	

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75834.



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